



Preface

The 3rd Asian Conference on Chemical Vapor Deposition (3rd Asian-CVD), Taipei, Taiwan, November 12–14, 2004

This special issue covers a part of invited and contributed papers, which were presented first at the 3rd Asian Conference on Chemical Vapor Deposition (3rd A-CVD), Taipei, Taiwan, ROC, November 12–14, 2004. Afterwards, they have gone through the usual procedure with regular papers in the journal, *Thin Solid Films*. At the 3rd A-CVD, 250 papers were presented. After strict referring and reviewing process, 110 papers have been selected for the publication as regular papers in two Elsevier journals, with 56 papers here at *Thin Solid Films* (TSF) and another part of 54 papers at *Surface and Coatings Technology* (SCT).

Same as the A-CVD conference scope, the special issue (and papers) provides a forum for current interest and significance of chemical vapor deposition and other growth technologies, preparation and characterization of electronic, optoelectronic, photonic and mechanical materials, their device applications and other film growth and nanostructure applications, as well as a wide range of attractive issues related to thin film technology. For the convenience of audience, the papers are divided into the following sub-groups: CVD: poly-Si and LT-Si; CVD: SiO₂, TiN, Al and

rate analysis; Cu-deposition; low and high *k* materials; GaN films: MOCVD; InGaN, AlGaIn, nitride QWs, QDs and detectors; ZnO epi-films; III–V semiconductor thin films; III–V QWs and QDs; carbon nanotubes; diamond-like and carbon films; OLED and related oxides; CoSi, Ta and F-glass films.

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